

D6-7-660-100



Application

Laser Projector
Measuring equipment

Property

Wavelength $\lambda = 660 \text{ nm}$
Output Power = 100mW
Package Type = $\varnothing 5.6\text{mm}$

Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers.

Laser Diode Key features

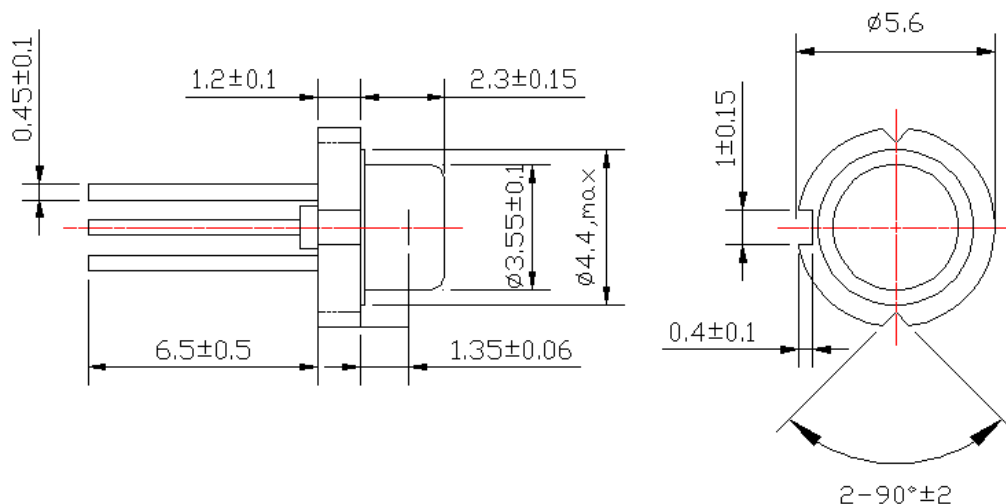
Absolute Maximum Rating at $T_c=25^\circ\text{C}$

Items	Symbols	Values	Unit
Operating Current power	P_o	100	mW
Reverse Voltage Laser diode	V_R	2	V
Operating Temperature	T_{case}	-10~+70	$^\circ\text{C}$
Storage Temperature	T_s	-40~+85	$^\circ\text{C}$

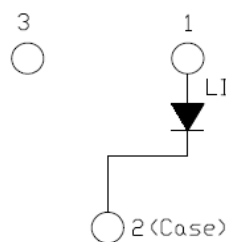
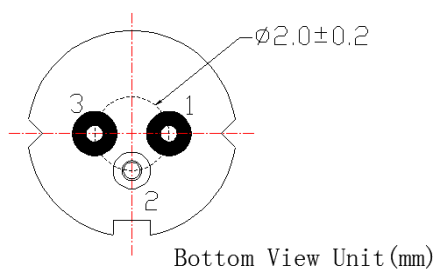
Electrical and Optical Characteristics at Tc=25°C

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	55	90	mA	-
Operating Current	I_{op}	-	140	250	mA	Po=100mW
Operating Voltage	V_{op}	-	2.5	3.5	V	Po=100mW
Peak Wavelength	λ_p	650	660	670	nm	Po=100mW
Beam Divergence (FWHM)	θ_r	7	-	13	deg	Po=100mW
Beam Divergence (FWHM)	θ_{\pm}	12	-	19	deg	Po=100mW

Package Drawing



Electrical Connection



Specifications are subject to change without notice.

